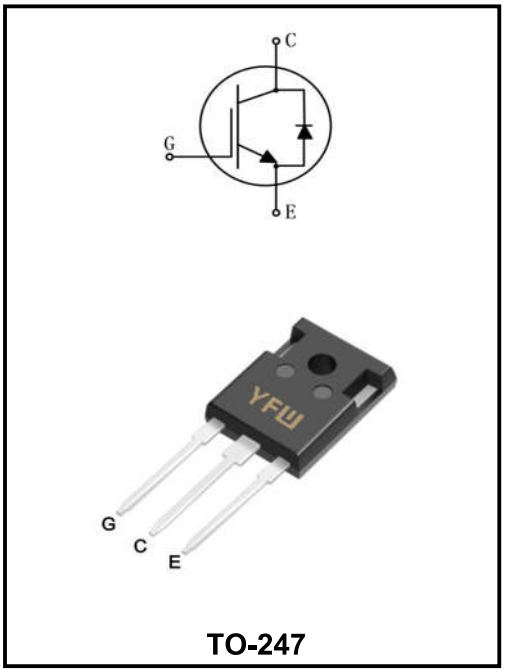
650V N-Channel Enhancement Mode Power IGBT

MAIN CHARACTERISTICS

$I_{C\ @TC=100℃}$	60A
V_{CE}	650V
VCE(sat)-typ	1.7V



TO-247

FEATURES

- Positive temperature coefficient
- Fast Switching
- Low VCE(sat)
- Reliable and Rugged

APPLICATIONS

- UPS
- Motor drives
- Boost
- Portable power station

MECHANICAL DATA

- Case: Molded plastic
- Mounting Position: Any
- Molded Plastic: UL Flammability Classification Rating 94V-0
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Solder bath temperature 275℃ maximum,10s per JESD 22-B106

Maximum Ratings

Characteristics	Symbol	Value	Unit
Collector-emitter voltage	V_{CES}	650	V
Gate-emitter voltage	V_{GES}	±30	V
Continuous collector current (TC=25℃)	I_C	120	A
Continuous collector current (TC=100℃)		60	A
Pulsed collector current, tp limited by Tvjmax	I_{CM}	240	A
Diode continuous forward current (TC=25℃)	I_F	120	A
Diode continuous forward current (TC=100℃)		60	A
Diode maximum current, tp limited by Tvjmax	I_{FM}	240	A
Operating junction temperature range	T_{vj}	-55 to +175	°C
Storage temperature range	T_{stg}	-55 to +175	°C

Thermal characteristics

Characteristics	Symbol	Values		Unit
		Typ	Max.	
Thermal resistance, junction to case for IGBT	$R_{th(j-c)}$	-	0.44	K/ W
Thermal resistance, junction to case for Diode	$R_{th(j-c)}$	-	0.49	K/ W
Thermal resistance, junction to ambient	$R_{th(j-a)}$	-	40	K/ W

Note1:Pulse test: 300 μs pulse width, 2 % duty cycle

Electrical characteristics of IGBT at Tvj=25℃ unless otherwise specified

Characteristics	Test Condition	Symbol	Min	Typ	Max	Unit
Collector-emitter breakdown voltage	V_{GE}=0V, I_C=250μA	B_{VCES}	650	-	-	V
Collector-emitter leakage current	V_{CE}=650V, V_{GE}=0V	I_{CES}	-	-	10	μA
Gate leakage current, forward	V_{GE}=±20V, V_{CE}=0V	I_{GES}	-	-	±100	nA
Gate-emitter threshold voltage	V_{GE}=V_{CE}, I_C=1mA	$V_{GE(th)}$	4.5	5.3	6.5	V
Collector-emitter saturation voltage	V_{GE}=15 V, I_C=60A	$V_{CE(sat)}$	-	1.7	2	V
	V_{GE}=15V, I_C=60A, T_{vj}=125℃		-	1.8	-	V
	V_{GE}=15V, I_C=60A, T_{vj}=175℃		-	2	-	V
Input capacitance	V_{CE}=25V V_{GE}=0V f =1MHz	C_{ies}	-	3363	-	pF
Output capacitance		C_{oes}	-	206	-	pF
Reverse transfer capacitance		C_{res}	-	92	-	pF
Total gate charge	V_{CC}=520V V_{GE}=15V I_C=60A	Q_g	-	179	-	nC
Gate- Emitter Charg		Q_{ge}	-	31	-	nC
Gate- Collector Charge		Q_{gc}	-	87	-	nC
Short circuit collector current Max.1000 short circuits, times between short circuits: ≥ 1.0s	V_{GE}=15V, V_{CC}≤400V t_{sc}≤8us T_J≤175°C	IC(SC)	-	430	-	A
Turn-on delay time	V_{CC}=400V V_{GE}=15V I_C=60A R_G=5Ω Inductive load	td(on)	-	26	-	ns
Rise time		tr	-	89	-	ns
Turn-off delay time		td(off)	-	128	-	ns
Fall time		tf	-	79	-	ns
Turn-on energy		Eon	-	1.42	-	mJ
Turn-off energy		Eoff	-	1.2	-	mJ
Total switching energy		Ets	-	2.62	-	mJ
Turn-on delay time	V_{CC}=400V V_{GE}=15V I_C=60A R_G=5Ω Inductive load Tvj =175℃	td(on)	-	37	-	ns
Rise time		tr	-	108	-	ns
Turn-off delay time		td(off)	-	159	-	ns
Fall time		tf	-	97	-	ns
Turn-on energy		Eon	-	1.72	-	mJ
Turn-off energy		Eoff	-	1.43	-	mJ
Total switching energy		Ets	-	3.15	-	mJ
Diode forward voltage	I_F=60A	VF	-	1.45	2.2	V
	I_F=60A,Tvj=125℃		-	1.26	-	V
	I_F=60A,Tvj=175℃		-	1.23	-	V
Diode reverse recovery time	V_R=400V I_F=60A diF/dt=-200A/μs	trr	-	110	-	ns
Diode peak reverse recovery current		Irrm	-	27	-	A
Diode reverse recovery charge		Qrr	-	1730	-	nC
Diode reverse recovery time	V_R=400V I_F=60A diF/dt=-200A/μsTvj=175℃	trr	-	104	-	ns
Diode peak reverse recovery current		Irrm	-	29	-	A
Diode reverse recovery charge		Qrr	-	1890	-	nC

RATINGS AND CHARACTERISTIC CURVES

Figure 1: Power Dissipation

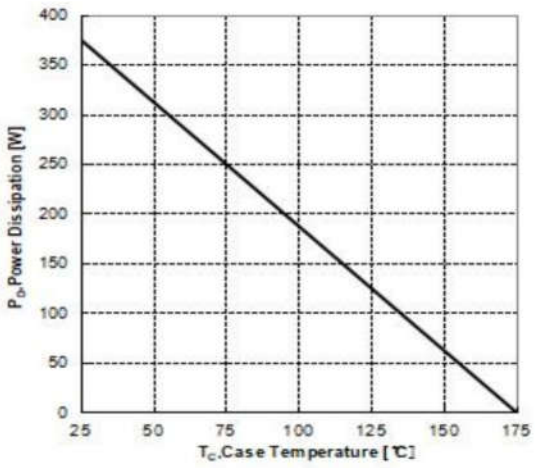


Figure 2: Collector Current vs. Case Temperature

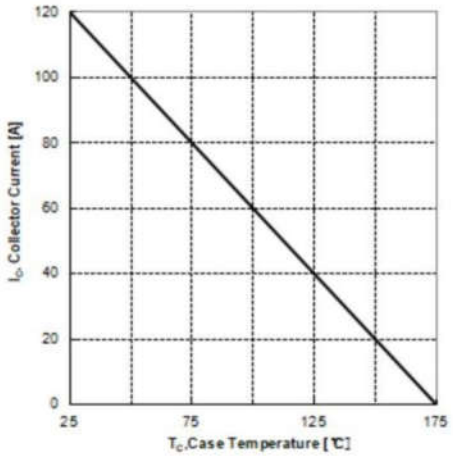


Figure 3: Safe Operation Area

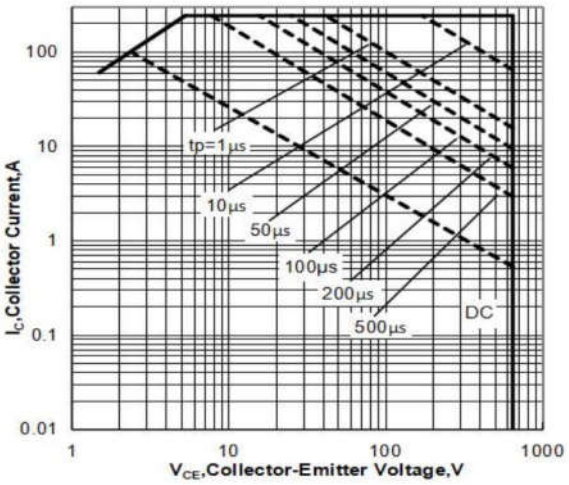


Figure 4: Typical Transfer Characteristics

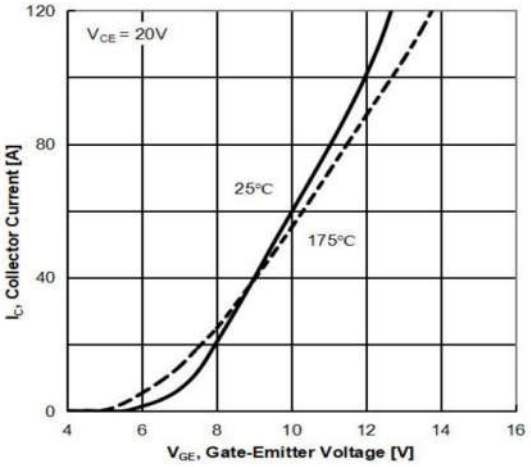


Figure 5: Typical Output Characteristics

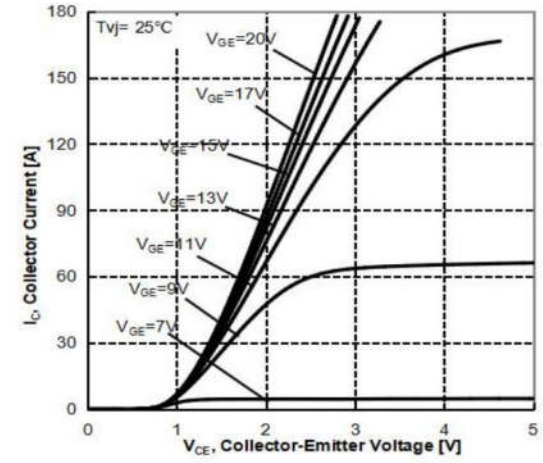


Figure 6: Typical Output Characteristics

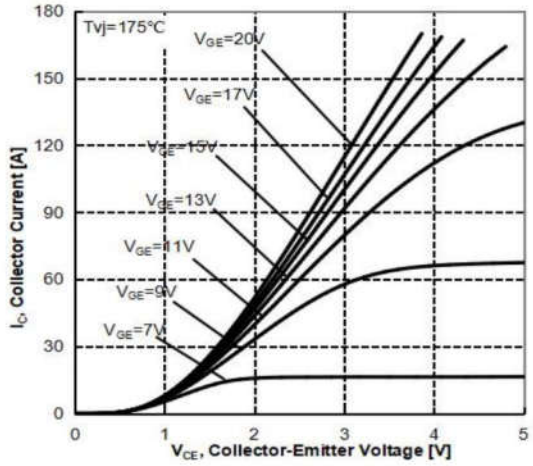


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Figure 7: Typical Collector-Emitter Saturation Voltage vs. Junction Temperature

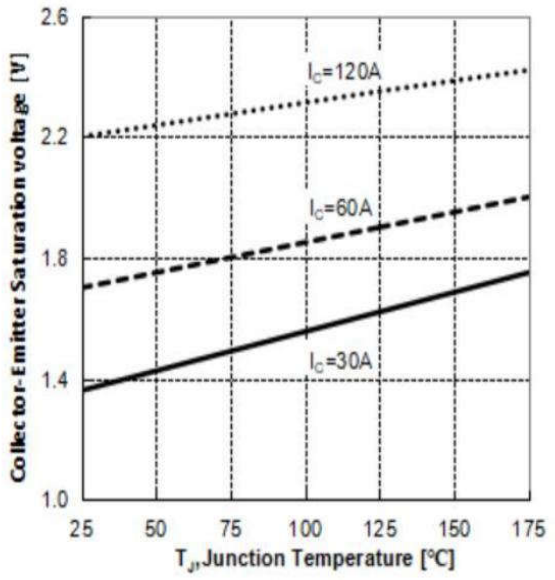

Figure 8: Typical Gate-Emitter Threshold Voltage vs. Junction Temperature

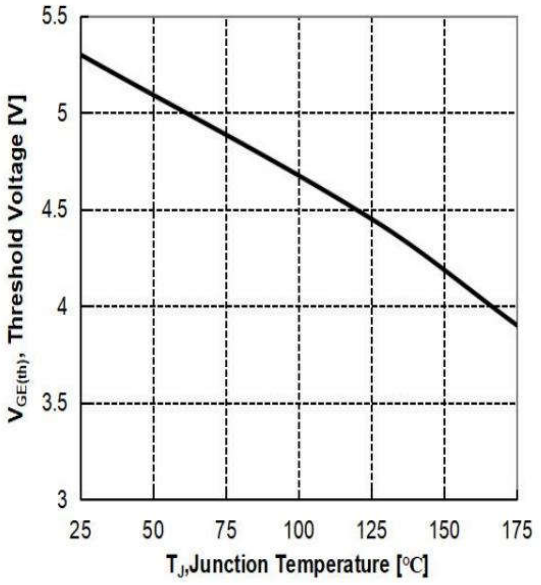

Figure 9: Typical Switching Times vs. Gate Resistor (T_J=25℃, V_{CE}=400V, V_{GE}=15/0V, I_C=60A)

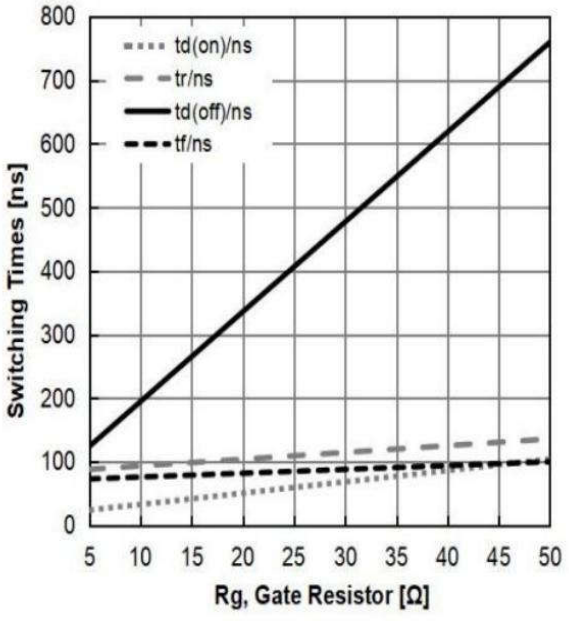

Figure 10: Typical Switching Energy vs. Gate Resistor (T_J=25℃, V_{CE}=400V, V_{GE}=15/0V, I_C=60A)

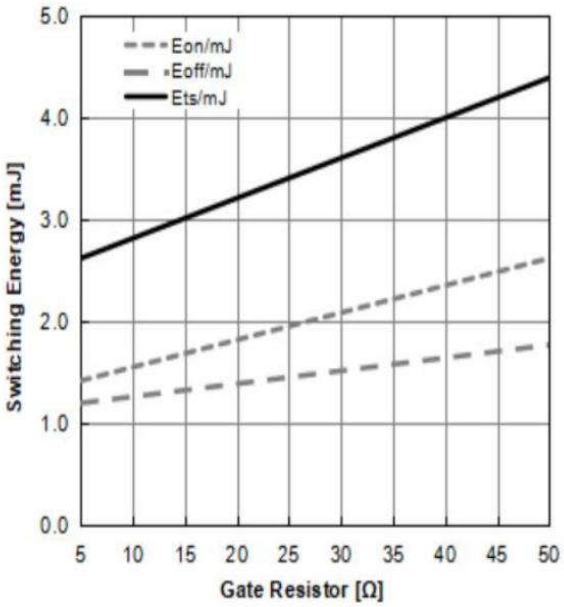

Figure 11: Typical Switching Times vs. Junction Temperature (V_{CE}=400V, V_{GE}=15/0V, I_C=60A)

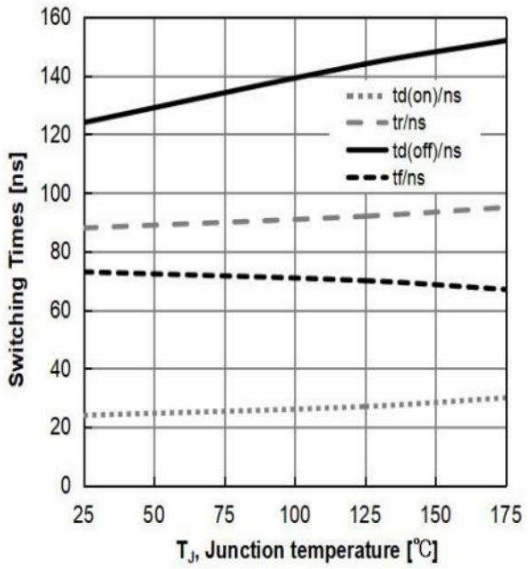

Figure 12: Typical Switching Energy vs. Junction Temperature (V_{CE}=400V, V_{GE}=15/0V, I_C=60A)

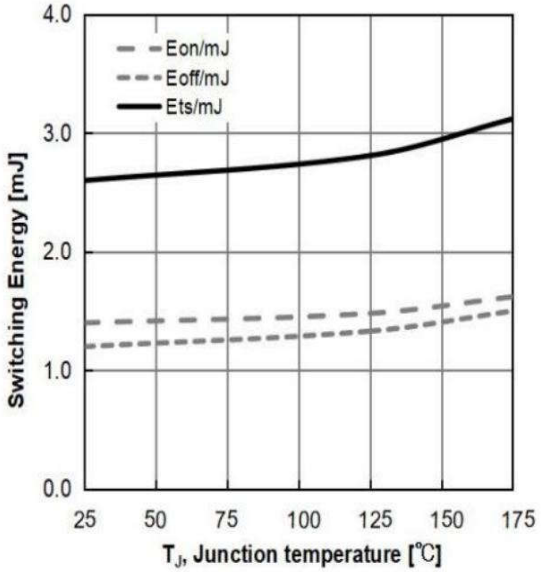

Figure 13: Typical Switching Times vs. Collector Current (T_J=25℃, V_{CE}=400V, V_{GE}=15/0V)

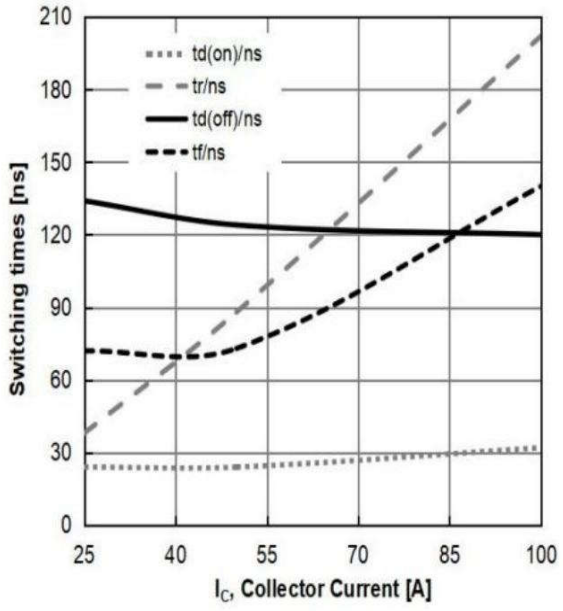

Figure 14: Typical Switching Energy vs. Collector Current (T_J=25℃, V_{CE}=400V, V_{GE}=15/0V)

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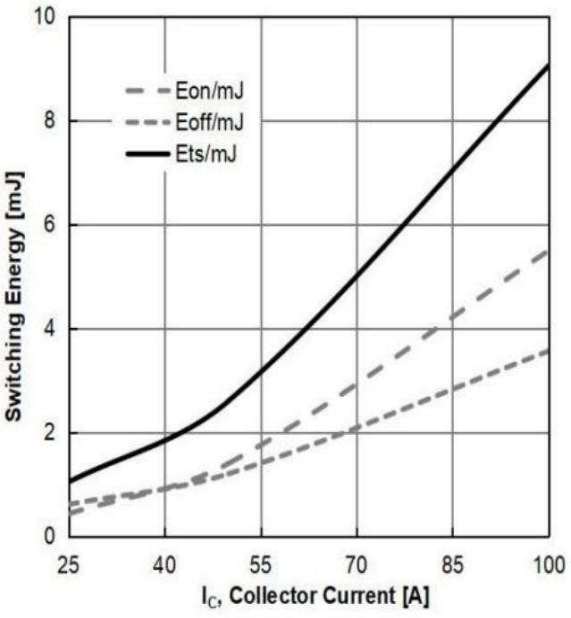

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Figure 15: Typical Switching Times vs. VCE (T_J=25℃,V_{GE}=15/0V, I_C=60A)

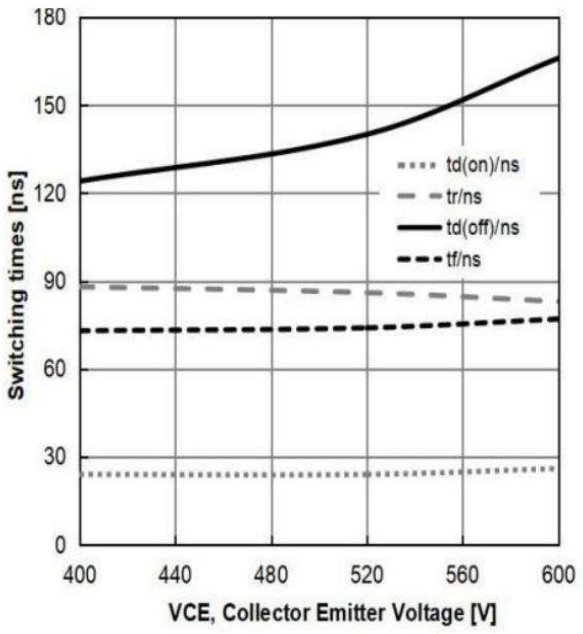


Figure 16: Typical Switching Energy vs. VCE (T_J=25℃, V_{GE}=15/0V, I_C=60A)

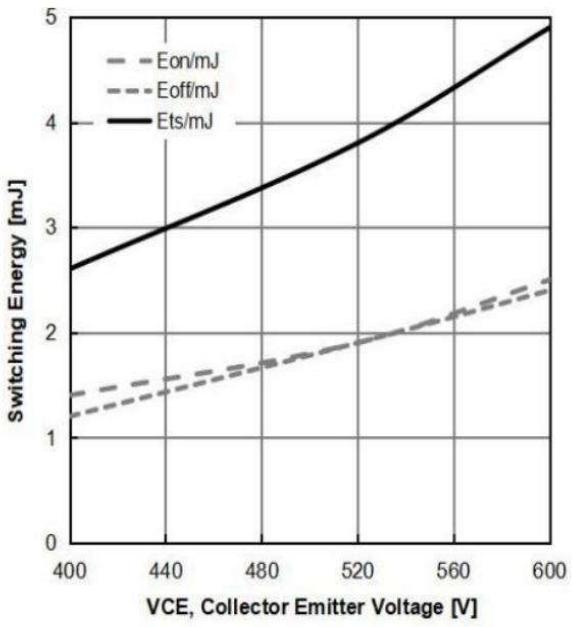


Figure 17: Typical Gate Charge

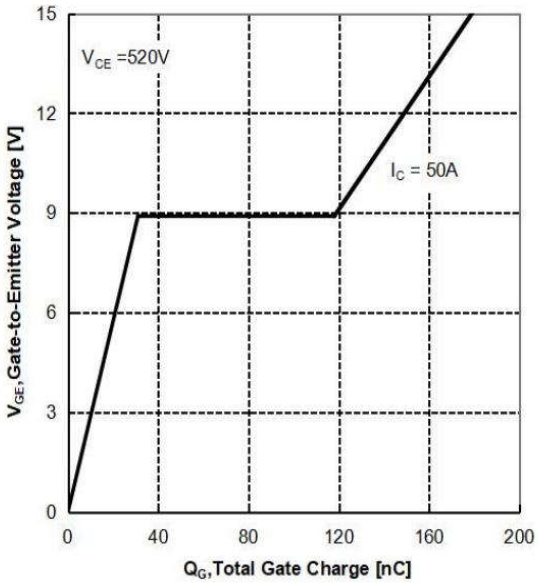
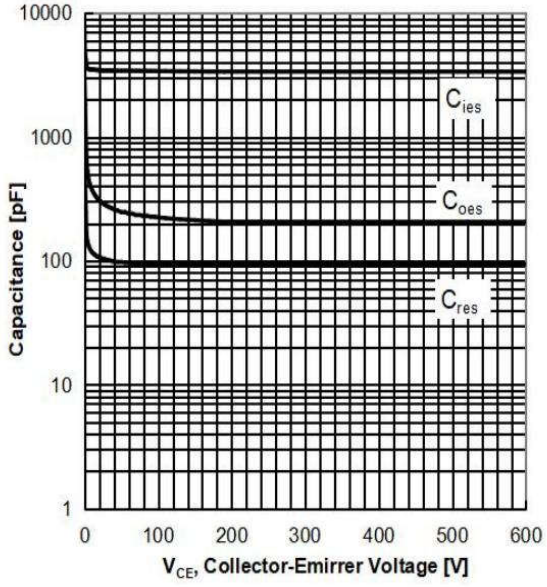


Figure 18: Typical Capacitance vs. Collector- Emitter Voltage



RATINGS AND CHARACTERISTIC CURVES

Figure 19: IGBT Transient Thermal Impedance vs. Pulse Width

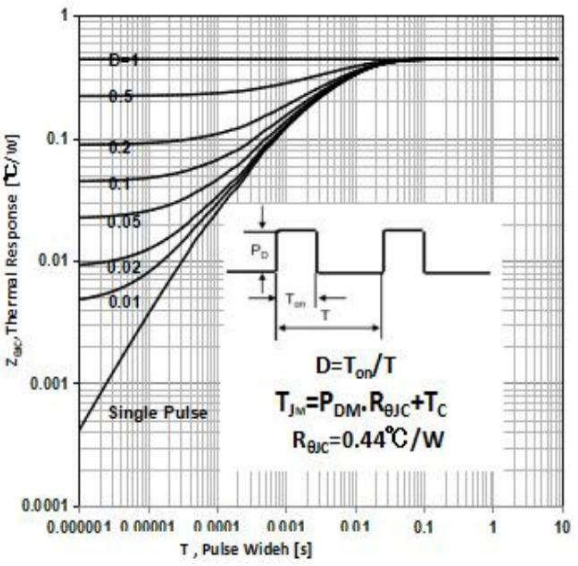


Figure 20: Diode Transient Thermal Impedance vs. Pulse Width

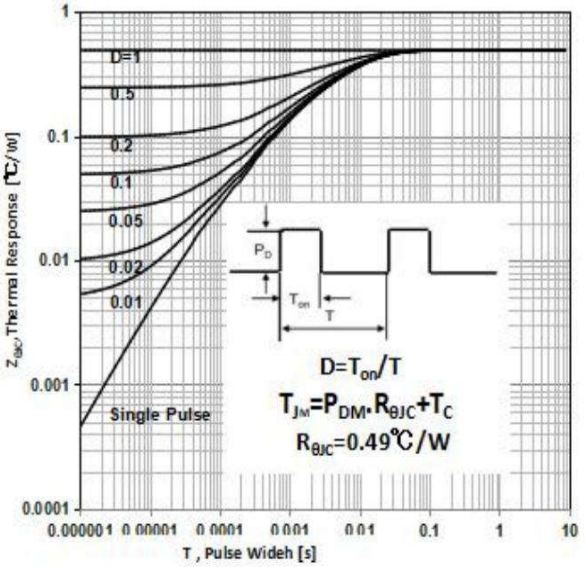
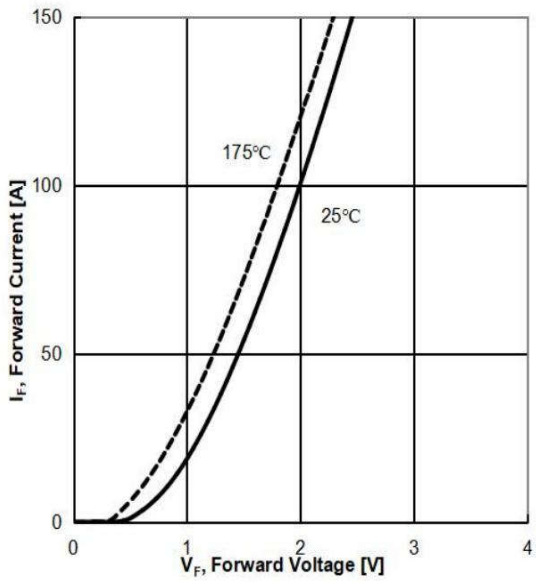
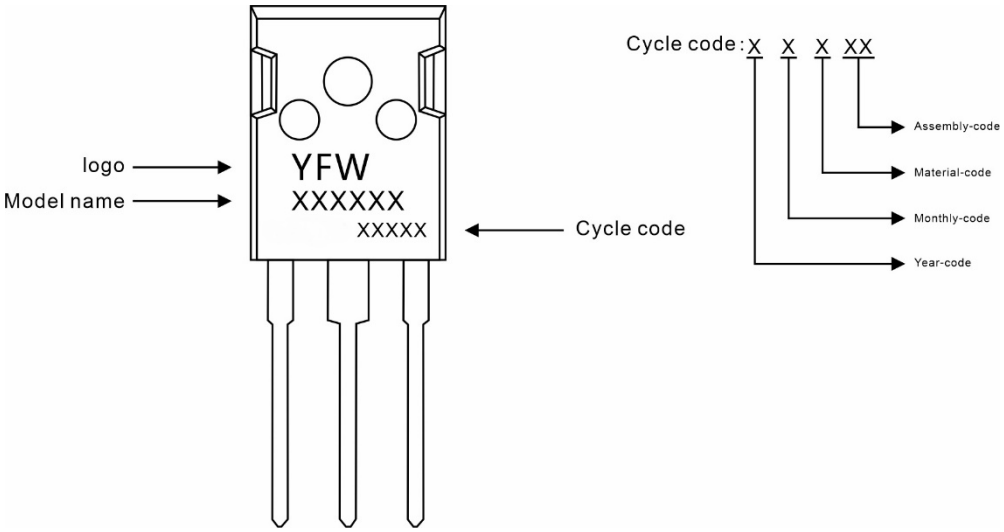


Figure 21: Typical Diode Forward Current vs. Forward Voltage



Marking Diagram

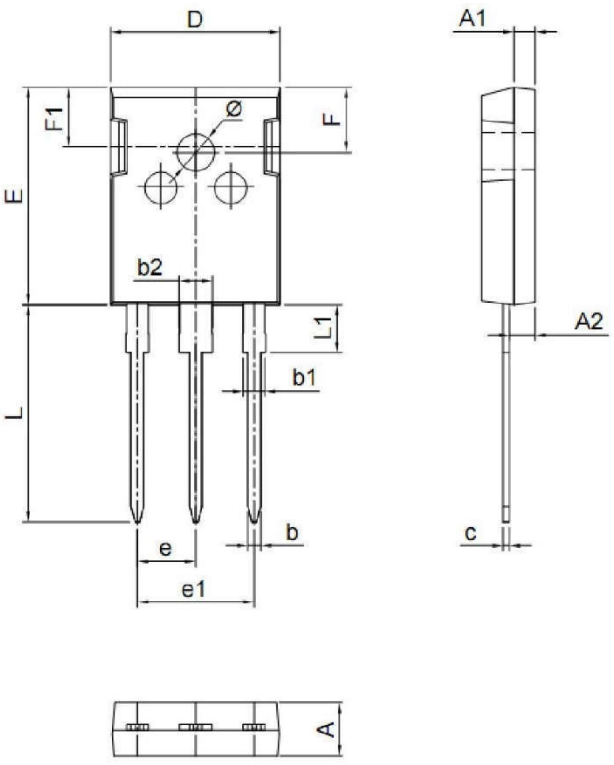


Ordering information

Model name	Package	Unit Weight	Base Quantity	Packing Quantity
YFWG60T65LAP	TO-247	0.209oz(5.93g)	30pcs/tube	600PCS/Box 2400PCS/Carton

Package Dimensions

TO-247



Symbol	Dimensions in mm		Dimensions in Inch	
	Min.	Max.	Min.	Max.
A	4.90	5.10	0.193	0.201
A1	1.90	2.10	0.075	0.083
A2	2.29	2.54	0.090	0.100
b	1.00	1.40	0.039	0.055
b1	2.00	2.20	0.079	0.087
b2	3.00	3.20	0.118	0.126
c	0.50	0.70	0.020	0.028
D	15.75	16.05	0.620	0.632
E	20.20	20.80	0.795	0.819
e	5.45 (BSC)		0.215 (BSC)	
e1	10.90 (BSC)		0.429 (BSC)	
F	6.05	6.25	0.238	0.246
F1	5.80	6.00	0.228	0.236
L	20.10	20.40	0.791	0.803
L1	4.05	4.35	0.159	0.171
Φ	3.50	3.70	0.138	0.146

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